IN THE CLAIMS

- (Original) A method, comprising:
 heating a stamper and a resist film;
 imprinting the stamper into the resist film;
 separating the stamper from the resist film; and
 cooling the resist film after the separating.
- 2. (Original) The method of claim 1, wherein the stamper and the resist film are heated to a temperature at least that of a glass transition temperature of the resist film.
- 3. (Original) The method of claim 1, wherein imprinting the stamper into the resist film comprises imprinting the stamper into the resist film to produce a pattern of trenches areas and plateau areas.
- 4. (Original) The method of claim 1, further comprising disposing the resist film above a base structure prior to the heating, wherein the base structure comprises a substrate.
- 5. (Original) The method of claim 4, further comprising selectively removing the resist film to form a pattern of areas above the base structure that do not have the resist film thereon.
- 6. (Original) The method of claim 5, further comprising disposing a magnetic layer above the base structure in the areas that do not have the resist film.
- 7. (Original) The method of claim 5, further comprising etching the base structure using the patterned resist film.

- 8. (Original) The method of claim 1, wherein the resist film comprises a single resist layer.
- 9. (Original) The method of claim 1, wherein the resist film comprises a plurality of resist layers.
- 10. (Original) The method of claim 2, further comprising preheating the resist film to the temperature.
- 11. (Original) The method of claim 1, wherein heating the stamper and the resist film comprises separately heating the stamper and the resist film.
- 12. (Original) The method of claim 11, wherein the stamper and the resist film are separately heated to an imprint temperature at least that of a glass transition temperature of the resist film.
- 13. (Original) The method of claim 12, further comprising placing the resist film in close proximity to the stamper while the resist film is approximately at the imprint temperature.

- 14. (Original) The method of claim 11, wherein the stamper is heated to a first temperature at least that of a glass transition temperature of the resist film and wherein the resist film is separately heated to a second temperature below that of the first temperature.
- 15. (Original) The method of claim 14, further comprising further heating the resist film to the first temperature.
- 16. (Original) The method of claim 11, wherein the stamper is heated to a first temperature at least that of a glass transition temperature of the resist film and wherein the resist film is separately heated to a second temperature above that of the first temperature.
- 17 (Original) A method, comprising:

heating a stamper and a resist film to a first temperature at least that of a transition temperature of the resist film;

imprinting the stamper into the resist film; cooling the resist film to a second temperature above room temperature; and separating the stamper from the resist film.

- 18. (Original) The method of claim 17, further comprising disposing the resist film above a base structure prior to the heating, wherein the base structure comprises a substrate.
- 19. (Original) The method of claim 17, further comprising:

selectively etching the resist film to form a pattern of areas above the base structure that do not have the resist film thereon; and

disposing a magnetic layer above the base structure in the areas that do not have the resist film.

- 20. (Original) The method of claim 17, wherein the resist film comprises a single resist layer.
- 21. (Original) The method of claim 17, wherein the resist film comprises a plurality of resist layers.
- 22. (New) The method of claim 1, wherein the resist film comprises a thermosetting material.
- 23. (New) The method of claim 7, further comprising removing the resist film, wherein a pattern of raised zones and recessed zones is formed in the base structure and wherein the method further comprising depositing a continuous film on the pattern of raised zones and recessed zones.
- 24. (New) The method of claim 23, wherein the resist film comprises a thermosetting material.